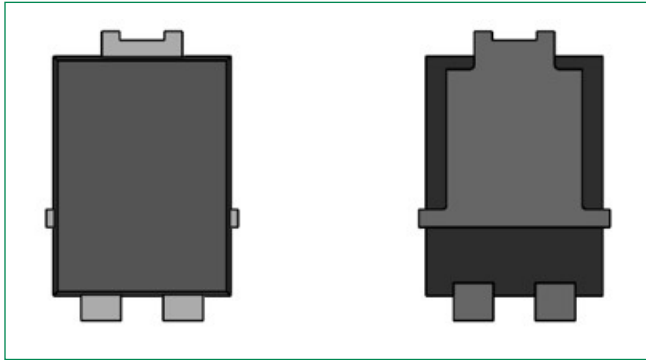
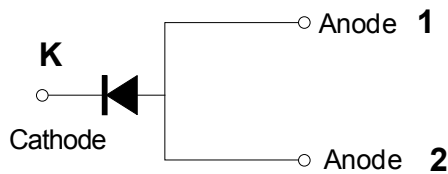


DST10100S-A



Pin out



Description

Littelfuse DST series Ultra Low V_F Schottky Barrier Rectifier is designed to meet the general requirements of Automotive applications by providing high temperature, low leakage and lower V_F products.

It is suitable for high frequency switching mode power supply, free-wheeling diodes and polarity protection diodes.

Features

- High reliability application and AEC-Q101 qualified.
- Ultra low forward voltage drop
- High frequency operation
- MSL: Level 1 - unlimited
- High junction temperature capability
- Trench MOS Schottky technology
- Single die in TO-277B Package
- Pb-free E3 means 2nd level interconnect is Pb-free and the terminal finish material is tin(Sn) (IPC/ JEDEC J-STD-609A.01)

Applications

- Switching mode power supply
- DC/DC converters
- Free-Wheeling diodes
- Polarity Protection Diodes

Maximum Ratings

Parameters	Symbol	Test Conditions	Max	Unit
Peak Inverse Voltage	V_{RWM}	-	100	V
Single Peak Reverse Voltage	V_{RSM}	-	105	V
Average Forward Current*	$I_{F(AV)}$	50% duty cycle @ $T_L = 125^\circ\text{C}$ rectangular wave form	10	A
Peak One Cycle Non-Repetitive Surge	I_{FSM}	8.3 ms, half Sine pulse	150	A

* Mounted on 30 mm x 30 mm pad areas aluminum PCB

Electrical Characteristics

Parameters	Symbol	Test Conditions	Max	Unit
Forward Voltage Drop *	V_{F1}	@2A, Pulse, $T_J = -40^\circ\text{C}$	0.60	V
	V_{F2}	@5A, Pulse, $T_J = -40^\circ\text{C}$	0.65	
	V_{F3}	@10A, Pulse, $T_J = -40^\circ\text{C}$	0.70	
	V_{F4}	@2A, Pulse, $T_J = 25^\circ\text{C}$	0.50	
	V_{F5}	@5A, Pulse, $T_J = 25^\circ\text{C}$	0.60	
	V_{F6}	@10A, Pulse, $T_J = 25^\circ\text{C}$	0.70	
	V_{F7}	@2A, Pulse, $T_J = 125^\circ\text{C}$	0.40	
	V_{F8}	@5A, Pulse, $T_J = 125^\circ\text{C}$	0.55	
	V_{F9}	@10A, Pulse, $T_J = 125^\circ\text{C}$	0.65	
Reverse Current *	I_{R1}	@ $V_R = \text{rated } V_R, T_J = 25^\circ\text{C}$	0.25	mA
	I_{R2}	@ $V_R = \text{rated } V_R, T_J = 125^\circ\text{C}$	36	

* Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications

Parameters	Symbol	Test Conditions	Max	Unit
Junction Temperature	T_J		-55 to +150	°C
Storage Temperature	T_{stg}		-55 to +150	°C
Maximum Thermal Resistance Junction to Ambient	R_{thJA}	DC operation	75	°C/W
Maximum Thermal Resistance Junction to Lead	R_{thJL}^*		3.5	°C/W
Approximate Weight	wt		0.08	g
Case Style		TO-277B		

*Lead temperature monitored at the cathode pin

Figure 1: Forward Current Derating Curve

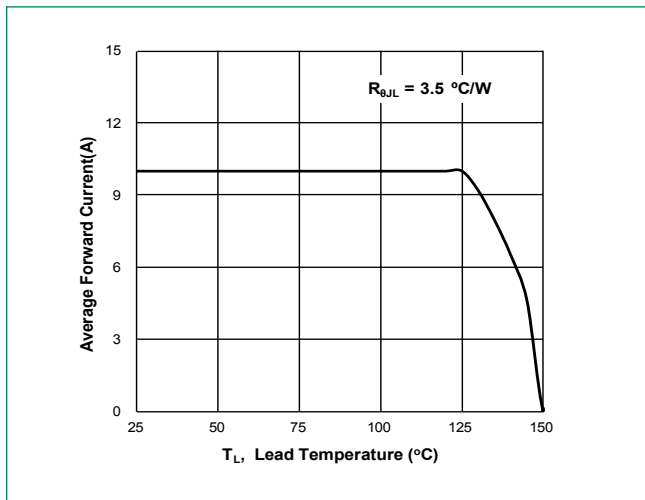


Figure 2: Forward Power Loss Characteristics

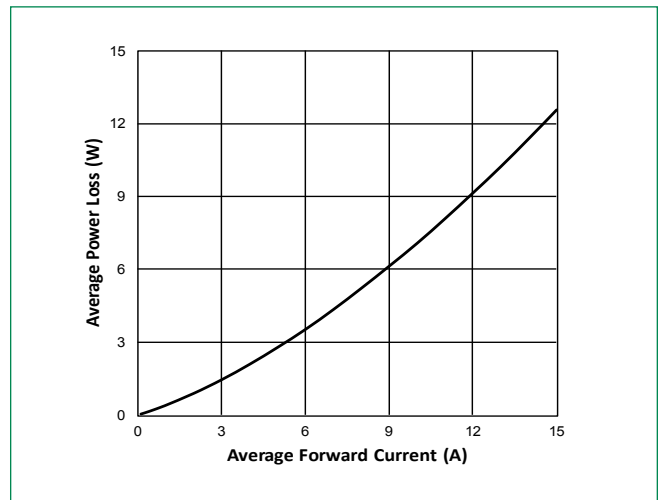


Figure 3: Typical Forward Characteristics

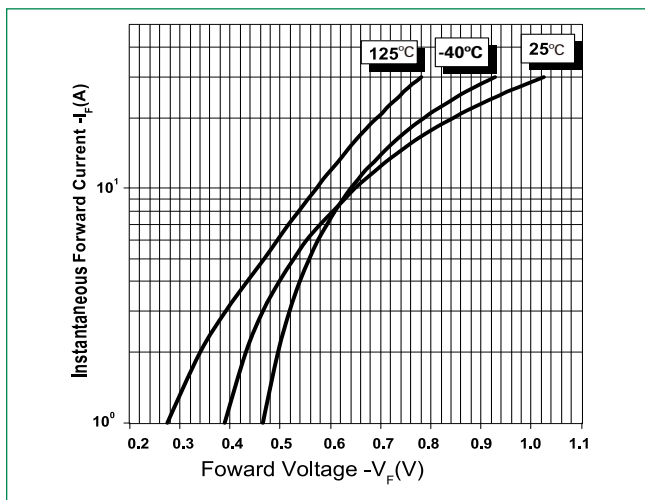


Figure 4: Typical Reverse Characteristics

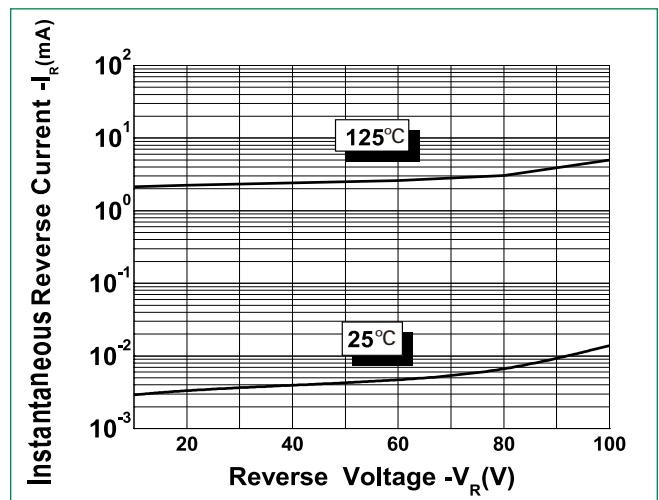
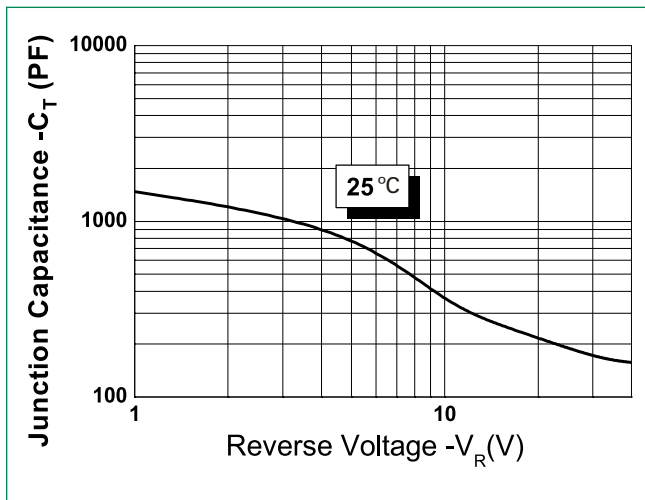
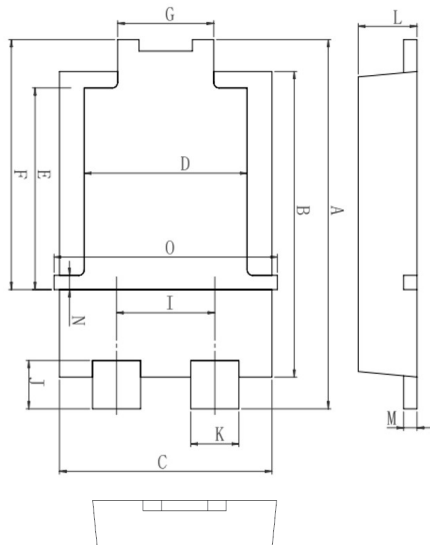


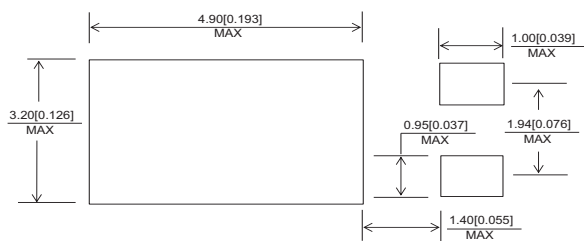
Figure 5: Typical Junction Capacitance



Dimensions-TO-277B



Mounting Pad Layout



Symbol	Millimeters		
	Min	Typ	Max
A	6.30	6.50	6.70
B	5.28	5.38	5.48
C	3.88	3.98	4.08
D	2.90	3.05	3.20
E	3.40	3.55	3.70
F	4.20	4.40	4.60
G	1.70	1.80	1.90
I	1.74	1.84	1.94
J	0.65	0.85	1.05
K	0.85	0.90	0.95
L	0.95	1.10	1.25
M	0.20	0.25	0.30
N	0.25	0.40	0.55
O	4.00	4.05	4.25

Part Numbering and Marking System

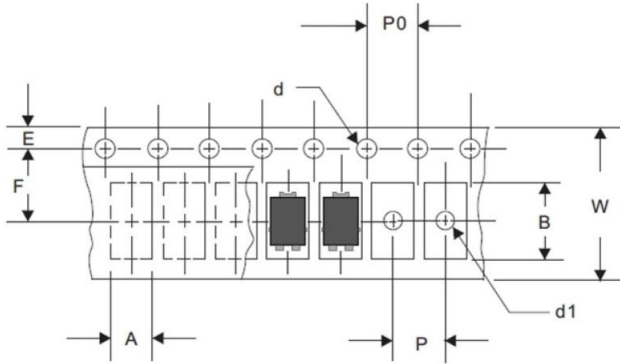


- DST = Device Type
- 10 = Forward Current (10A)
- 100 = Reverse Voltage (100V)
- S = Package Type
- A = AEC-Q101 qualified device
- LF = Littelfuse
- YY = Year
- WW = Week
- L = Lot Number

Packing Options

Part Number	Marking	Packing Mode	M.O.Q
DST10100S-A	DST10100S-A	5000pcs / Reel	5000

Carrier Tape & Reel Specification



Symbol	Millimeters	
	Min	Max
A	4.28	4.48
B	6.80	7.00
d	1.40	1.60
d1	-	1.50
E	1.65	1.85
F	7.40	7.60
P	5.40	5.60
P0	3.90	4.10
W	11.70	12.30